

# RJK6026DPE

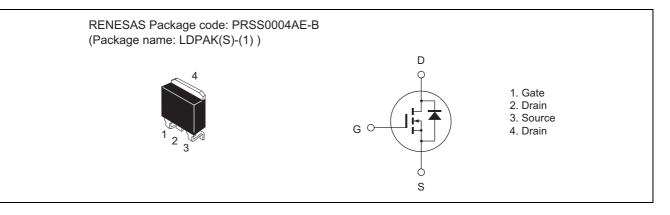
Silicon N Channel MOS FET High Speed Power Switching

> REJ03G1479-0100 Rev.1.00 Jul 02, 2009

# Features

- Low on-resistance
- Low leakage current
- High speed switching

### Outline



# **Absolute Maximum Ratings**

 $(Ta = 25^{\circ}C)$ Item Symbol Ratings Unit Drain to source voltage V<sub>DSS</sub> 600 V V Gate to source voltage V<sub>GSS</sub> ±30 5 A Drain current  $I_D$ Note1 20 Drain peak current A Body-drain diode reverse drain current  $I_{DR}$ 5 A 20 Body-drain diode reverse drain peak current I<sub>DR (pulse)</sub> А I<sub>AP</sub><sup>Note3</sup> Avalanche current 4 A E<sub>AR</sub><sup>Note3</sup> 0.87 Avalanche energy mJ Pch Note2 W Channel dissipation 62.5 Channel to case thermal impedance θch-c 2 °C/W 150 Channel temperature Tch °C °C Storage temperature Tstg -55 to +150

Notes: 1.  $PW \le 10 \ \mu s$ , duty cycle  $\le 1\%$ 

2. Value at Tc = 25°C

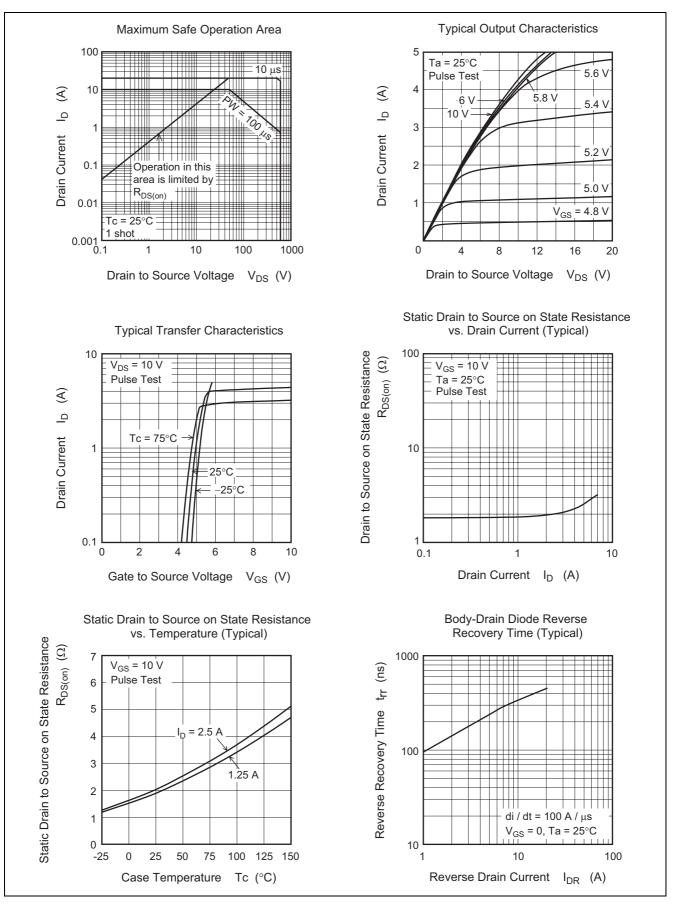
3. STch =  $25^{\circ}$ C, Tch  $\leq 150^{\circ}$ C

# **Electrical Characteristics**

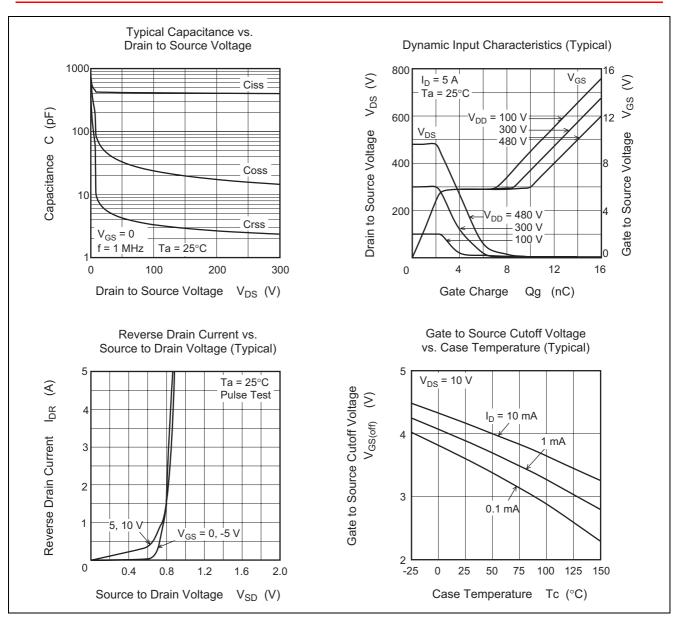
						$(Ta = 25^{\circ}C)$
Item	Symbol	Min	Тур	Max	Unit	Test conditions
Drain to source breakdown voltage	V <sub>(BR)DSS</sub>	600	—	—	V	$I_D = 10 \text{ mA}, V_{GS} = 0$
Zero gate voltage drain current	I <sub>DSS</sub>	—	—	1	μΑ	$V_{DS} = 600 \text{ V}, V_{GS} = 0$
Gate to source leak current	I <sub>GSS</sub>	_	_	±0.1	μΑ	$V_{GS} = \pm 30$ V, $V_{DS} = 0$
Gate to source cutoff voltage	V <sub>GS(off)</sub>	3.0	_	4.5	V	$V_{DS} = 10 \text{ V}, \text{ I}_{D} = 1 \text{ mA}$
Static drain to source on state resistance	R <sub>DS(on)</sub>	_	2.0	2.4	Ω	$I_D = 2.5 \text{ A}, V_{GS} = 10 \text{ V}^{Note4}$
Input capacitance	Ciss	_	440	_	pF	V <sub>DS</sub> = 25 V
Output capacitance	Coss	_	45	_	pF	V <sub>GS</sub> = 0 f = 1 MHz
Reverse transfer capacitance	Crss	_	6	_	pF	
Turn-on delay time	t <sub>d(on)</sub>	_	26	_	ns	I <sub>D</sub> = 2.5 A
Rise time	tr	_	18		ns	$V_{GS} = 10 V$ $R_L = 120 \Omega$ $Rg = 10 \Omega$
Turn-off delay time	t <sub>d(off)</sub>	_	53		ns	
Fall time	t <sub>f</sub>	_	14	_	ns	
Total gate charge	Qg	_	14	_	nC	V <sub>DD</sub> = 480 V
Gate to source charge	Qgs	_	3	_	nC	V <sub>GS</sub> = 10 V I <sub>D</sub> = 5 A
Gate to drain charge	Qgd	_	7		nC	
Body-drain diode forward voltage	V <sub>DF</sub>	_	0.9	1.5	V	$I_F = 5 \text{ A}, V_{GS} = 0^{Note4}$
Body-drain diode reverse recovery time	t <sub>rr</sub>	_	250		ns	$I_F = 5 \text{ A}, V_{GS} = 0$ $di_F/dt = 100 \text{ A}/\mu \text{s}$

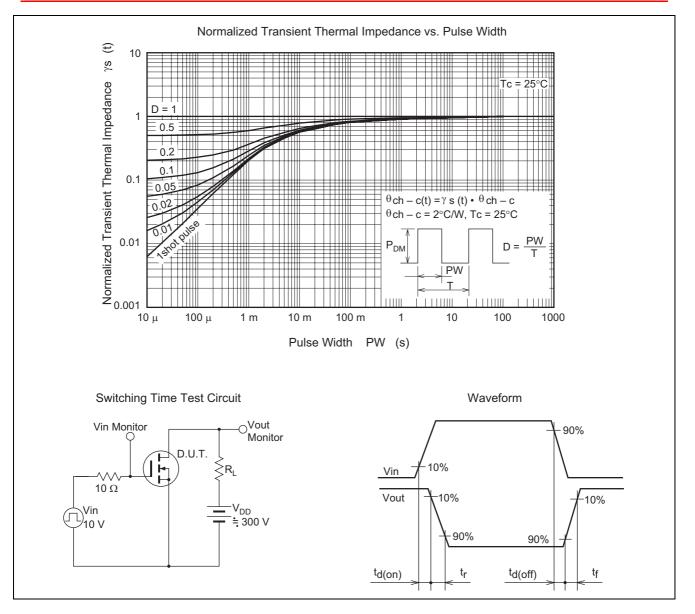
Notes: 4 Pulse test

### **Main Characteristics**



RENESAS





# Package Dimensions

Package Name	JEITA Package Code	RENESAS Code	Previous Code	MASS[Typ.]	Unit: mm
DPAK(S)-(1)	SC-83	PRSS0004AE-B LDP/	AK(S)-(1) / LDPAK(S)-(1)V	1.30g	Offic. Hill
	1.3 ± 0.2 2.54 ± 0.5	$\pm 0.3$ $(7, 1)$ $(7$		<u> </u>	

# **Ordering Information**

Part No.	Quantity	Shipping Container
RJK6026DPE-00-J3	1000 pcs	Taping

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